

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	205840	CAN NEAR3 SUBSTRATE	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:48
L3	7576	CAN NEAR3 SEMICONDUCTOR NEAR3 MATERIAL	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:53
L4	364	3 AND "372"/\$.CCLS.	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:50
L5	7576	"CaN" NEAR3 SEMICONDUCTOR NEAR3 MATERIAL	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:50
L6	364	5 AND "372"/\$.CCLS.	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:51
L7	7	calcium near3 nitride near3 substrate	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:52
L8	0	calcium near3 nitride NEAR3 SEMICONDUCTOR NEAR3 MATERIAL	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:53
L9	1	calcium near3 nitride NEAR3 SEMICONDUCTOR	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:54
L10	9	calcium near3 nitride and "372"/\$.ccls.	US-PGPUB; USPAT	OR	OFF	2006/11/01 16:54
L11	1	("5966396").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/01 18:11
L12	204	nitride near3 laser and ridge and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/11/01 18:36
L13	293	nitride near3 laser and (ridge or stripe) and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/11/01 18:48
L14	12	nitride near3 laser and (ridge or stripe) and mesa and ((smooth\$3 or round\$3 or curv\$3) near3 (corner or cleavage))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/11/01 18:49
S1	16	semiconductor near3 laser same round\$3 near3 corner\$1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 19:27

EAST Search History

S2	18	semiconductor near3 laser and round\$3 near3 corner\$1 and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 18:27
S3	10	semiconductor near3 laser and curv\$6 near3 corner\$1 and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 18:31
S4	10	(scrib\$3 near3 force near3 (prevent\$3 or suppression or attenuation or reduc\$4 or eliminat\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 19:49
S5	2	((("4476563") or ("5966396")).PN.	US-PGPUB; USPAT	OR	OFF	2006/10/31 18:34
S6	13	("20010015448" "20030038294" "20030162342" "20030209717" "20030227065" "20040229429" "5807774" "5990500" "6100174" "6139780" "6284654" "6475321").PN. OR ("6921928").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/31 18:58
S7	1147	372/43.01.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 19:49
S8	132	S7 and mesa and (ridge or stripe)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 19:50
S9	11	semiconductor near3 laser and current near3 injection near3 ridge and ((passivat\$3 or protect\$3) near3 (layer or coat\$3 or film)) and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 21:19
S10	4	semiconductor near3 laser and mesa and smooth near3 cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 21:13

EAST Search History

S11	21	semiconductor near3 laser and smooth near3 cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 21:17
S12	8	"372"/\$.ccls. and smooth near3 cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 21:17
S13	407	semiconductor near3 laser and ridge and ((passivat\$3 or protect\$3) near3 (layer or coat\$3 or film)) and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/11/01 18:36
S14	114	semiconductor near3 laser and ridge and ((passivat\$3) near3 (layer or coat\$3 or film)) and mesa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2006/10/31 21:20